

A substrate processing method comprises providing a substrate **105** comprising etch resistant material **210** in a process zone **155**, such as an energized gas zone in a process chamber **110**. The etch resistant material **210** may comprise a resist material **230** over mask material **240**. The process may further comprise removing the etch resistant material **210**, such as the resist material **230**, in the process zone **155** before etching underlying layers.